

2N3467  
2N3468

**SILICON  
PNP TRANSISTORS**



**TO-39 CASE**



[www.centrasemi.com](http://www.centrasemi.com)

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR 2N3467 and 2N3468 are silicon PNP switching transistors designed for core driver applications.

**MARKING: FULL PART NUMBER**

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

Collector-Base Voltage	
Collector-Emitter Voltage	
Emitter-Base Voltage	
Continuous Collector Current	
Power Dissipation	
Power Dissipation ( $T_C=25^\circ\text{C}$ )	
Operating and Storage Junction Temperature	
Thermal Resistance	
Thermal Resistance	

SYMBOL	2N3467	2N3468	UNITS
$V_{CBO}$	40	50	V
$V_{CEO}$	40	50	V
$V_{EBO}$		5.0	V
$I_C$		1.0	A
$P_D$		1.0	W
$P_D$		5.0	W
$T_J, T_{stg}$	-65 to +200		$^\circ\text{C}$
$\theta_{JA}$	175		$^\circ\text{C/W}$
$\theta_{JC}$	35		$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N3467		2N3468		UNITS
		MIN	MAX	MIN	MAX	
$I_{CBO}$	$V_{CB}=30\text{V}$	-	100	-	100	nA
$I_{CBO}$	$V_{CB}=30\text{V}, T_A=100^\circ\text{C}$	-	15	-	15	$\mu\text{A}$
$I_{CEV}$	$V_{CE}=30\text{V}, V_{BE}=3.0\text{V}$	-	100	-	100	nA
$I_{BEV}$	$V_{CE}=30\text{V}, V_{BE}=3.0\text{V}$	-	120	-	120	nA
$BV_{CBO}$	$I_C=10\mu\text{A}$	40	-	50	-	V
$BV_{CEO}$	$I_C=10\text{mA}$	40	-	50	-	V
$BV_{EBO}$	$I_E=10\mu\text{A}$	5.0	-	5.0	-	V
$V_{CE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$	-	0.3	-	0.36	V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$	-	0.5	-	0.6	V
$V_{CE(SAT)}$	$I_C=1.0\text{A}, I_B=100\text{mA}$	-	1.0	-	1.2	V
$V_{BE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$	-	1.0	-	1.0	V
$V_{BE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$	0.8	1.2	0.8	1.2	V
$V_{BE(SAT)}$	$I_C=1.0\text{A}, I_B=100\text{mA}$	-	1.6	-	1.6	V
$h_{FE}$	$V_{CE}=1.0\text{V}, I_C=150\text{mA}$	40	-	25	-	
$h_{FE}$	$V_{CE}=1.0\text{V}, I_C=500\text{mA}$	40	120	25	75	
$h_{FE}$	$V_{CE}=5.0\text{V}, I_C=1.0\text{A}$	40	-	20	-	

R2 (26-July 2013)

2N3467  
2N3468

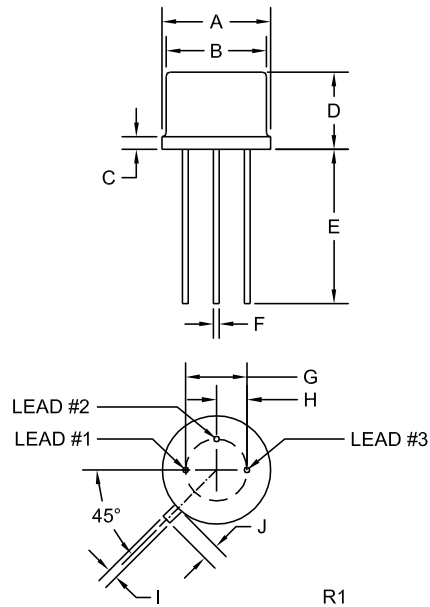
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**ELECTRICAL CHARACTERISTICS - Continued:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N3467		2N3468		UNITS
		MIN	MAX	MIN	MAX	
$f_T$	$V_{CE}=10\text{V}$ , $I_C=50\text{mA}$ , $f=100\text{MHz}$	175	-	150	-	MHz
$C_{ob}$	$V_{CB}=10\text{V}$ , $I_E=0$ , $f=100\text{kHz}$	-	25	-	25	pF
$C_{ib}$	$V_{EB}=0.5\text{V}$ , $I_C=0$ , $f=100\text{kHz}$	-	100	-	100	pF
$t_{on}$	$V_{CC}=30\text{V}$ , $V_{BE}=2.0\text{V}$ , $I_C=500\text{mA}$ , $I_{B1}=50\text{mA}$	-	40	-	40	ns
$t_{off}$	$V_{CC}=30\text{V}$ , $I_C=500\text{mA}$ , $I_{B1}=I_{B2}=50\text{mA}$	-	90	-	90	ns
$Q_T$	$V_{CC}=30\text{V}$ , $I_C=500\text{mA}$ , $I_B=50\text{mA}$	-	6.0	-	6.0	nC

**TO-39 CASE - MECHANICAL OUTLINE**



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.335	0.370	8.51	9.40
B (DIA)	0.315	0.335	8.00	8.51
C	-	0.040	-	1.02
D	0.240	0.260	6.10	6.60
E	0.500	-	12.70	-
F (DIA)	0.016	0.021	0.41	0.53
G (DIA)	0.200		5.08	
H	0.100		2.54	
I	0.028	0.034	0.71	0.86
J	0.029	0.045	0.74	1.14

TO-39 (REV: R1)

**LEAD CODE:**

- 1) Emitter
- 2) Base
- 3) Collector

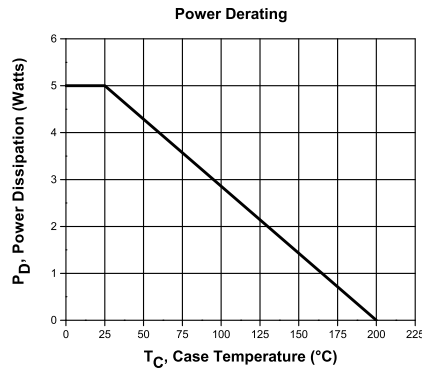
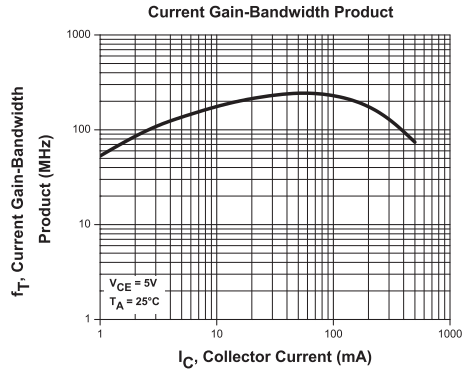
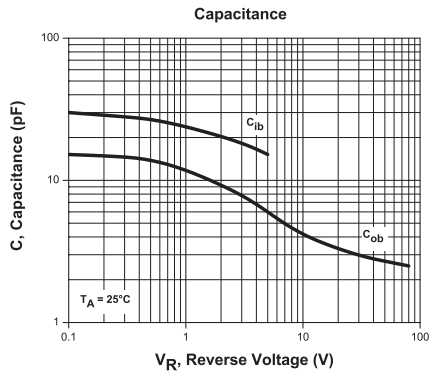
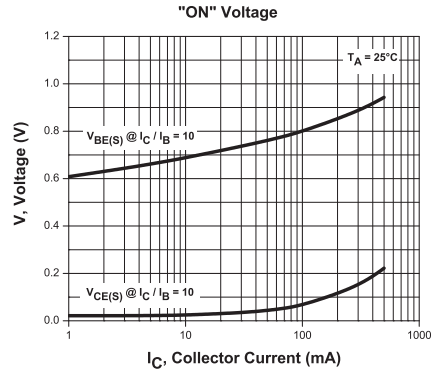
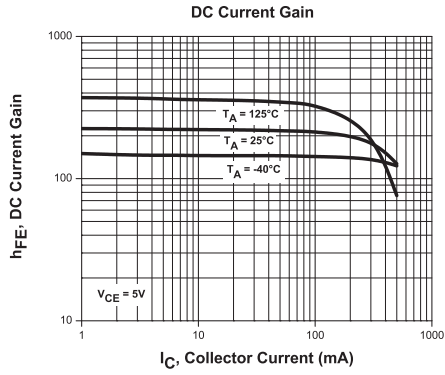
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TYPICAL ELECTRICAL CHARACTERISTICS



R2 (26-July 2013)